AMENDMENTS TO THE CLAIMS

1. (currently amended) A light-emitting apparatus, comprising:

a primary light source including a GaN semiconductor light-emitting device that emits light of a wavelength of 380 nm to 500 nm, said GaN semiconductor light-emitting device, including:

a single reflective layer disposed on a surface of a substrate on which no light-emitting layer is formed; and

a transparent electrode disposed above said single reflective layer; and

a secondary light source including a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; and Y_2O_2S:Ce,

wherein said fluorescent material absorbs light of a first wavelength, emitted by said primary light source, and emits light of a second wavelength, which is greater than said first wavelength.

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2. (previously amended) A light-emitting apparatus according to claim 1, wherein

said fluorescent material is dispersed in a light-transmissible layer, which is disposed above said primary light source,

a part of said light emitted by said primary light source is transmitted through said light-transmissible layer, and

another part of said light emitted by said primary light source is absorbed by said fluorescent material, said fluorescent material then emits light, and said light emitted by said fluorescent material and said light emitted by said primary light source are mixed, to thereby generate a light, emitted from said light-emitting apparatus, that is different in luminescent color from said light emitted by said primary light source.

3. (previously amended) A light-emitting apparatus according to claim 2, wherein said light-transmissible layer comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

4. (canceled)

5. (currently amended) A light-emitting apparatus according to claim 3, wherein a sealing member is disposed above said light-transmissible layer and ~~said~~ a leadframe.

6. (previously amended) A light-emitting apparatus according to claim 5, wherein said sealing member comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

7. (original) A light-emitting apparatus according to claim 5, wherein said sealing member is shaped like a bullet.

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8. (previously amended) A light-emitting apparatus according to claim 2, wherein a concentration of said fluorescent material changes within said light-transmissible layer, as a function of distance to said GaN semiconductor light-emitting device.

9. (previously amended) A light-emitting apparatus according to claim 5, wherein said light-transmissible layer and said sealing member comprise one material.

10. (previously amended) A light-emitting apparatus according to claim 2, wherein said GaN semiconductor light-emitting device comprises a chip.

11. (currently amended) A light-emitting apparatus, comprising:

a primary light source including a GaN semiconductor light-emitting device that emits light of a wavelength of 380 nm to 500 nm, said GaN semiconductor light-emitting device, including:

a single reflective layer disposed on a surface of a substrate on which no semiconductor layer is formed; and

a transparent electrode disposed above said single reflective layer; and

a secondary light source including a fluorescent material that comprises at least one of ZnS:Eu and Y_2O_2S:Ce,

wherein said fluorescent material absorbs light of a first wavelength, emitted by said primary light source, and emits light of a second wavelength, which is greater than said first wavelength.

12. (previously amended) A light-emitting apparatus according to claim 11, wherein

said fluorescent material is dispersed in a light-transmissible layer, which is disposed above said primary light source,

a part of said light emitted by said primary light source is transmitted through said light-transmissible layer, and

another part of said light emitted by said primary light source is absorbed by said fluorescent material, said fluorescent material then emits light, and said light emitted by said fluorescent material and said light emitted by said primary light source are mixed, to thereby generate a light, emitted from said light-emitting apparatus, that is different in luminescent color from said light emitted by said primary light source.

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13. (previously amended) A light-emitting apparatus according to claim 12, wherein said light-transmissible layer comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

14. (canceled)

15. (currently amended) A light-emitting apparatus according to claim 13, wherein a sealing member is disposed above said light-transmissible layer and ~~said~~ a leadframe.

16. (previously amended) A light-emitting apparatus according to claim 15, wherein said sealing member comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

17. (original) A light-emitting apparatus according to claim 15, wherein said sealing member is shaped like a bullet.

18. (previously amended) A light-emitting apparatus according to claim 12, wherein a concentration of said fluorescent material changes within said light-transmissible layer, as a function of distance to said GaN semiconductor light-emitting device.

19. (previously amended) A light-emitting apparatus according to claim 15, wherein said

light-transmissible layer and said sealing member are comprise one material.

20. (previously amended) A light-emitting apparatus according to claim 12, wherein said GaN semiconductor light-emitting device is a chip.

21. (currently amended) A light-emitting apparatus, comprising:

a first light source including a GaN semiconductor light-emitting device that emits blue light, said GaN semiconductor light-emitting device, including:

a single reflective layer disposed on a surface of a substrate on which no semiconductor layer is formed; and

a transparent electrode disposed above said single reflective layer; and

a second light source including a first fluorescent material that absorbs light emitted by said first light source and emits green light; and

a third light source that emits red light,

wherein said blue light emitted by said first light source, said green light emitted by said second light source, and said red light emitted by said third light source are mixed to thereby generate white light.

22. (previously amended) A light-emitting apparatus according to claim 21, wherein said first fluorescent material comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; ZnS:Eu; and Y_2O_2S:Ce.

23. (canceled)

24. (canceled)

25. (original) A light-emitting apparatus according to claim 21, wherein said third light source includes a semiconductor light-emitting device for emitting red light.

26. (previously amended) A light-emitting apparatus according to claim 41, wherein said first fluorescent material and said second fluorescent material are dispersed in a

light-transmissible layer, which is disposed above said GaN semiconductor light-emitting device,

a part of said blue light emitted by said first light source is transmitted through said light-transmissible layer, and

another part of said blue light emitted by said first light source is absorbed by said first fluorescent material, which emits said green light, and said second fluorescent material, which emits said red light, and said blue light emitted by said first light source, said green light emitted by said first fluorescent material, and said red light emitted by said second fluorescent material are mixed, to thereby generate a light, emitted from said light-emitting apparatus, different in luminescent color from the said blue light emitted from said first light source.

27. (previously amended) A light-emitting apparatus according to claim 26, wherein said light-transmissible layer comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

28. (previously amended) A light-emitting apparatus according to claim 26, wherein said light-transmissible layer is disposed above said GaN semiconductor light-emitting device.

29. (currently amended) A light-emitting apparatus according to claim 28, wherein a sealing member is disposed above said light-transmissible layer and ~~said~~ a leadframe.

30. (previously amended) A light-emitting apparatus according to claim 29, wherein said sealing member comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

31. (original) A light-emitting apparatus according to claim 29, wherein said sealing member is shaped like a bullet.

32. (previously amended) A light-emitting apparatus according to claim 26, wherein a concentration of at least one of said first fluorescent material and said second fluorescent material changes within said light-transmissible layer, as a function of distance to said GaN

semiconductor light-emitting device.

33. (previously amended) A light-emitting apparatus according to claim 29, wherein said light-transmissible layer and said sealing member comprise one material.

34. (previously amended) A light-emitting apparatus according to claim 26, wherein said GaN semiconductor light-emitting device comprises a chip.

35. (canceled)

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37. (canceled)

38. (previously presented) The light-emitting apparatus according to claim 1, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

39. (previously presented) The light-emitting apparatus according to claim 11, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

40. (previously presented) The light-emitting apparatus according to claim 21, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.,

41. (previously presented) A light-emitting apparatus according to claim 21, wherein said third light source includes a second fluorescent material that absorbs light emitted by said first light source and emits red light.

42. (currently amended) A light-emitting apparatus, comprising:

a box including a bottom surface including a first electrode and a second electrode;

a primary light source including a GaN semiconductor light-emitting device that emits light of a wavelength of 380 nm to 500 nm and is fixed to one of said first electrode and said

second electrode, said GaN semiconductor light-emitting device, including:

a single reflective layer disposed on a surface of a substrate on which no light-emitting layer is formed; and

a transparent electrode disposed above said single reflective layer; and

a secondary light source including a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; and ZnS:Cu,

wherein said fluorescent material absorbs light of a first wavelength, emitted by said primary light source, and emits light of a second wavelength, which is greater than said first wavelength.

43. (currently amended) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

two LEDs from a group of a red LED[[;]], a green LED[[;]], and a blue LED; and

a light-emitting apparatus according to claim 1.

44. (currently amended) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

two LEDs from a group of a red LED[[;]], a green LED[[;]], and a blue LED; and

a light-emitting apparatus according to claim 11.

45. (currently amended) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

two LEDs from a group of a red LED[[;]], a green LED[[;]], and a blue LED;

a light-emitting apparatus according to claim 41.

46. (previously presented) A vehicular signal display device comprising a plurality of light-emitting apparatuses according to claim 1, wherein said plurality of light-emitting apparatuses comprise a matrix, a portion of said matrix being controlled by a controller, which turns said portion on or off.

47. (canceled)

48. (canceled)

49. (previously presented) A light-emitting apparatus according to claim 1, wherein said fluorescent material is dispersed in a light-transmissible layer that is disposed above a sealing member, which is disposed above and focuses said light emitted said GaN semiconductor light-emitting device.

50. (previously presented) A light-emitting apparatus according to claim 41, wherein said first fluorescent material is dispersed in a first light-transmissible layer, which is disposed directly above said GaN semiconductor light-emitting device, and a second fluorescent material is dispersed in a second light-transmissible layer, which is disposed on said first light-transmissible layer.